

-55V P-Channel Enhancement Mode MOSFET

Description

The SX6P05SI uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = -60V I_{D} = -6.8A$

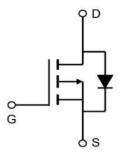
 $R_{DS(ON)}$ < 125m Ω @ Vgs=-10V

Application

Battery protection

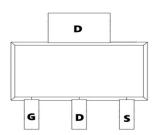
Load switch

Uninterruptible power supply









Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter Rating		Units	
VDS	Drain-Source Voltage	ource Voltage -55		
VGS	Gate-Source Voltage	Gate-Source Voltage ±20		
lo@Ta=25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-6.8	А	
lo@Ta=70°C	Continuous Drain Current, V _{GS} @ -10V ¹	'GS @ -10V ¹ -4.4		
IDM	Pulsed Drain Current ²	-16	А	
Pb@Ta=25°C	Total Power Dissipation ³	1	W	
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}$ C	
Tu	Operating Junction Temperature Range	-55 to 150	${\mathbb C}$	
R₀JA	Thermal Resistance Junction-Ambient ¹	125	°C/W	
R⊕JC	Thermal Resistance Junction-Case ¹	80 °C/W		

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Electrical Characteristics (TC=25 ℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , In=-250uA	-55	-58		V
∆BVDSS/∆T J	BV _{DSS} Temperature Coefficient	Reference to 25 [°] C ,lɒ=-1mA		-0.021		V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	Vgs=-10V , Ip=-1.5A		110	125	mΩ
TEO(OIV)	V _{GS} =-4.5V , I _D =-1A			125	155	mΩ
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	1.6	-2.5	V
$\triangle V$ GS(th)	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID250UA		4.08		mV/℃
IDSS	Dunin Course Lookers Courset	V _{DS} =-48V , V _{GS} =0V , T _J =25℃			1	
IDSS	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =55°C			5	- uA
IGSS	Gate-Source Leakage Current	Vgs=±20V , Vps=0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-1.5A		5.9		s
Qg	Total Gate Charge (-4.5V)	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-1.5A		4.6		nC
Qgs	Gate-Source Charge			1.4		nC
Qgd	Gate-Drain Charge			1.62		nC
Td(on)	Turn-On Delay Time			17.4		ns
Tr	Rise Time	V _{DS} =-15V , V _{GS} =-10V , R _G =3.3Ω,		5.4		ns
Td(off)	Turn-Off Delay Time	ID=-1A		37.2		ns
Tf	Fall Time			2.4		ns
Ciss	Input Capacitance			531		pF
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		59		pF
Crss	Reverse Transfer Capacitance			38		pF
IS	Continuous Source Current ^{1,4}	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			-1.7	Α
ISM	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			-7	Α
VSD	Diode Forward Voltage ²	Vgs=0V , Is=-1A , Tյ=25℃			-1.2	V

Note:

- 1. The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width $\,\, \leqq \, 300 us$, duty cycle $\,\, \leqq \, 2\%$
- 3 . The power dissipation is limited by $150\,^\circ\!\mathrm{C}\text{junction}$ temperature
- $4\sqrt{100}$ The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

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Typical Characteristics

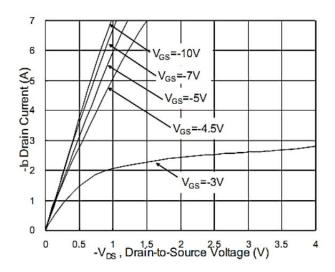


Fig.1 Typical Output Characteristics

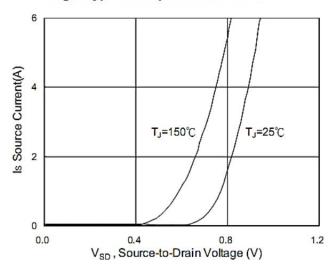


Fig.3 Forward Characteristics Of Reverse

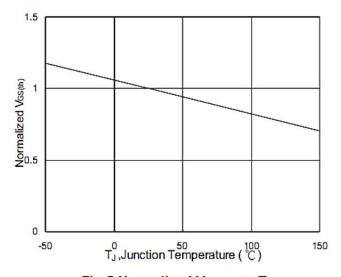


Fig.5 Normalized V_{GS(th)} v.s T_J

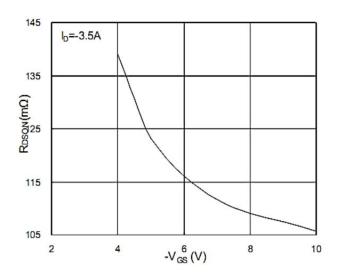


Fig.2 On-Resistance v.s Gate-Source

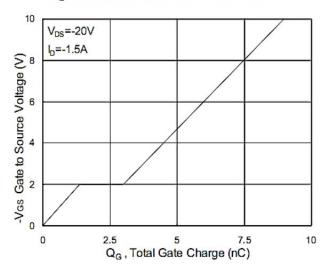


Fig.4 Gate-Charge Characteristics

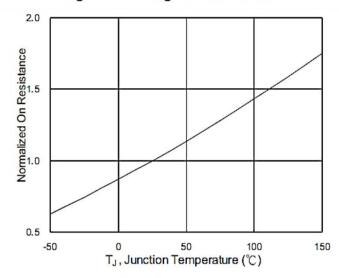
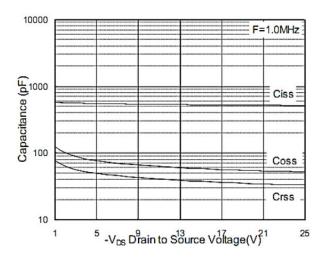


Fig.6 Normalized RDSON v.s TJ





Typical Characteristics



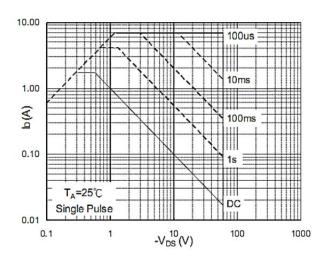


Fig.7 Capacitance

Fig.8 Safe Operating Area

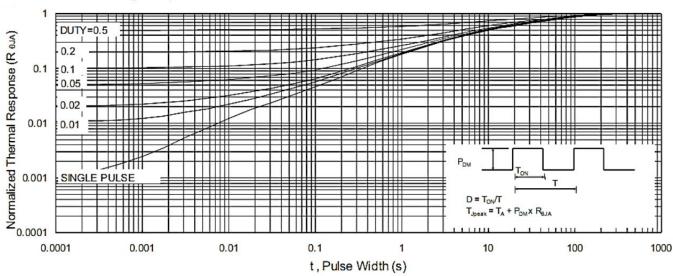


Fig.9 Normalized Maximum Transient Thermal Impedance

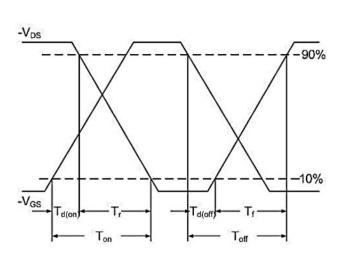


Fig.10 Switching time waveform

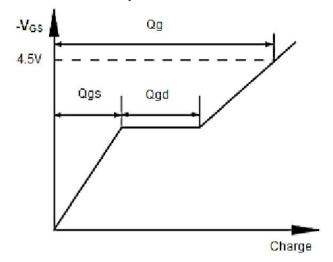
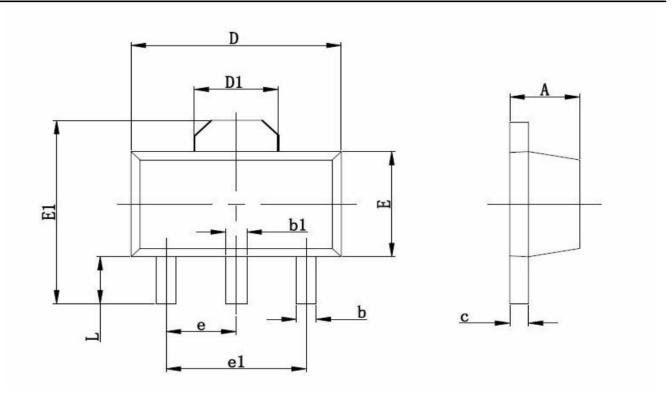


Fig.11 Gate Charge waveform





Package Mechanical Data:SOT89-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.350	0.520	0.013	0.197	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF		0.061 REF		
E	2.350	2.550	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP		0.060TYP		
e1	3.000 TYP		0.11	8TYP	
L	0.900	1.100	0.035	0.047	

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT89-3L		3000

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